



April 2015

# FGH20N60SFDTU\_F085

## 600 V, 20 A Field Stop IGBT

### Features

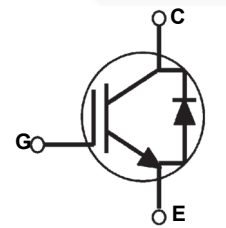
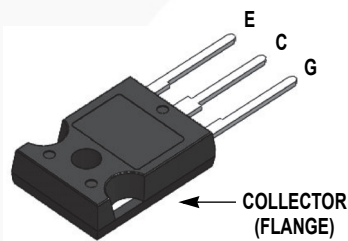
- High Current Capability
- Low Saturation Voltage:  $V_{CE(sat)} = 2.2\text{ V @ } I_C = 20\text{ A}$
- High Input Impedance
- Fast Switching
- RoHS Compliant
- Qualified to Automotive Requirements of AEC-Q101

### General Description

Using Novel Field Stop IGBT Technology, Fairchild's new series of Field Stop IGBTs offer the optimum performance for Automotive Chargers, Inverter, and other applications where low conduction and switching losses are essential.

### Applications

- Automotive chargers, Converters, High Voltage Auxiliaries
- Inverters, PFC, UPS



### Absolute Maximum Ratings

Symbol	Description	Ratings	Unit
$V_{CES}$	Collector to Emitter Voltage	600	V
$V_{GES}$	Gate to Emitter Voltage	$\pm 20$	V
	Transient Gate-to-Emitter Voltage	$\pm 30$	
$I_C$	Collector Current @ $T_C = 25^\circ\text{C}$	40	A
	Collector Current @ $T_C = 100^\circ\text{C}$	20	A
$I_{CM(1)}$	Pulsed Collector Current @ $T_C = 25^\circ\text{C}$	60	A
$P_D$	Maximum Power Dissipation @ $T_C = 25^\circ\text{C}$	165	W
	Maximum Power Dissipation @ $T_C = 100^\circ\text{C}$	66	
$T_J$	Operating Junction Temperature	-55 to +150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	-55 to +150	$^\circ\text{C}$
$T_L$	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds	300	$^\circ\text{C}$

**Notes:**

1: Repetitive rating: Pulse width limited by max. junction temperature

### Thermal Characteristics

Symbol	Parameter	Typ.	Unit
$R_{\theta JC}(\text{IGBT})$	Thermal Resistance, Junction to Case	0.76	$^\circ\text{C/W}$
$R_{\theta JC}(\text{Diode})$	Thermal Resistance, Junction to Case	2.51	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	40	$^\circ\text{C/W}$

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## Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FGH20N60SFDTU_F085	FGH20N60SFD	TO-247	Tube	N/A	N/A	30

## Electrical Characteristics of the IGBT T<sub>C</sub> = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
<b>Off Characteristics</b>						
$BV_{CES}$	Collector to Emitter Breakdown Voltage	$V_{GE} = 0\text{ V}, I_C = 250\ \mu\text{A}$	600	-	-	V
$\Delta BV_{CES}$ $\Delta T_J$	Temperature Coefficient of Breakdown Voltage	$V_{GE} = 0\text{ V}, I_C = 250\ \mu\text{A}$	-	0.6	-	V/°C
$I_{CES}$	Collector Cut-Off Current	$V_{CE} = V_{CES}, V_{GE} = 0\text{ V}$	-	-	250	$\mu\text{A}$
$I_{GES}$	G-E Leakage Current	$V_{GE} = V_{GES}, V_{CE} = 0\text{ V}$	-	-	±400	nA
<b>On Characteristics</b>						
$V_{GE(th)}$	G-E Threshold Voltage	$I_C = 250\ \mu\text{A}, V_{CE} = V_{GE}$	4.0	4.6	6.5	V
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C = 20\text{ A}, V_{GE} = 15\text{ V}$	-	2.2	2.8	V
		$I_C = 20\text{ A}, V_{GE} = 15\text{ V},$ $T_C = 125^\circ\text{C}$	-	2.4	-	V
<b>Dynamic Characteristics</b>						
$C_{ies}$	Input Capacitance	$V_{CE} = 30\text{ V}, V_{GE} = 0\text{ V},$ $f = 1\text{ MHz}$	-	985	-	pF
$C_{oes}$	Output Capacitance		-	110	-	pF
$C_{res}$	Reverse Transfer Capacitance		-	40	-	pF
<b>Switching Characteristics</b>						
$t_{d(on)}$	Turn-On Delay Time	$V_{CC} = 400\text{ V}, I_C = 20\text{ A},$ $R_G = 10\ \Omega, V_{GE} = 15\text{ V},$ Inductive Load, $T_C = 25^\circ\text{C}$	-	13	-	ns
$t_r$	Rise Time		-	18	-	ns
$t_{d(off)}$	Turn-Off Delay Time		-	90	-	ns
$t_f$	Fall Time		-	20	48	ns
$E_{on}$	Turn-On Switching Loss		-	0.43	-	mJ
$E_{off}$	Turn-Off Switching Loss		-	0.13	-	mJ
$E_{ts}$	Total Switching Loss		-	0.56	-	mJ
$t_{d(on)}$	Turn-On Delay Time	$V_{CC} = 400\text{ V}, I_C = 20\text{ A},$ $R_G = 10\ \Omega, V_{GE} = 15\text{ V},$ Inductive Load, $T_C = 125^\circ\text{C}$	-	13	-	ns
$t_r$	Rise Time		-	16	-	ns
$t_{d(off)}$	Turn-Off Delay Time		-	95	-	ns
$t_f$	Fall Time		-	50	-	ns
$E_{on}$	Turn-On Switching Loss		-	0.53	-	mJ
$E_{off}$	Turn-Off Switching Loss		-	0.24	-	mJ
$E_{ts}$	Total Switching Loss		-	0.77	-	mJ
$Q_g$	Total Gate Charge	$V_{CE} = 400\text{ V}, I_C = 20\text{ A},$ $V_{GE} = 15\text{ V}$	-	66	-	nC
$Q_{ge}$	Gate to Emitter Charge		-	7	-	nC
$Q_{gc}$	Gate to Collector Charge		-	33	-	nC

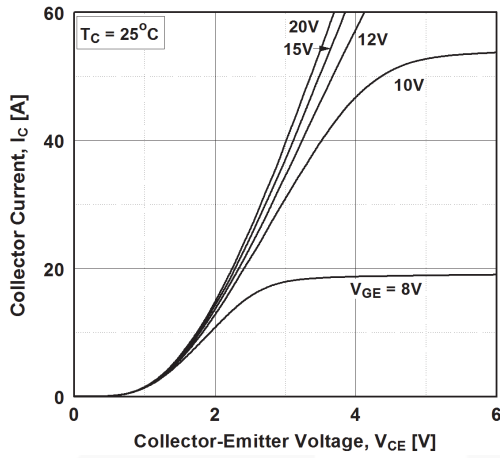
**Electrical Characteristics of the Diode**  $T_C = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max	Unit	
$V_{FM}$	Diode Forward Voltage	$I_F = 10\text{ A}$	$T_C = 25^\circ\text{C}$	-	1.9	2.5	V
			$T_C = 125^\circ\text{C}$	-	1.7	-	
$t_{rr}$	Diode Reverse Recovery Time	$I_F = 10\text{ A}, di_F/dt = 200\text{ A}/\mu\text{s}$	$T_C = 25^\circ\text{C}$	-	40	-	ns
			$T_C = 125^\circ\text{C}$	-	180	-	
$Q_{rr}$	Diode Reverse Recovery Charge	$I_F = 10\text{ A}, di_F/dt = 200\text{ A}/\mu\text{s}$	$T_C = 25^\circ\text{C}$	-	70	-	nC
			$T_C = 125^\circ\text{C}$	-	495	-	

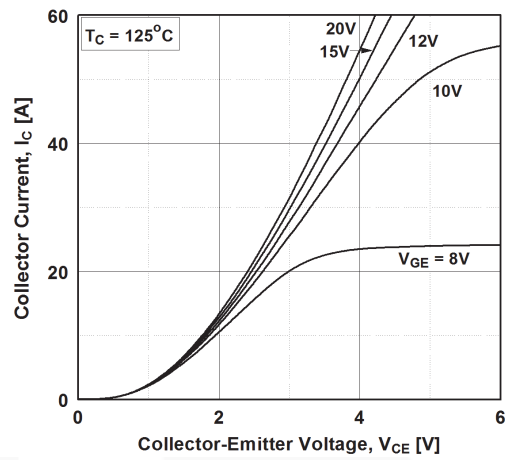


## Typical Performance Characteristics

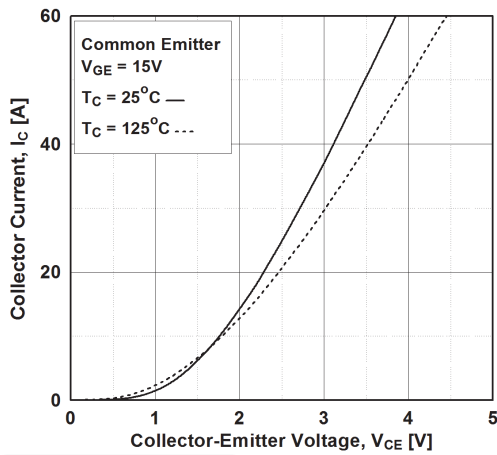
**Figure 1. Typical Output Characteristics**



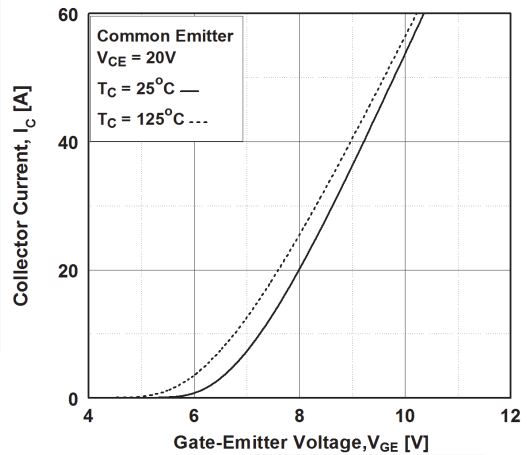
**Figure 2. Typical Output Characteristics**



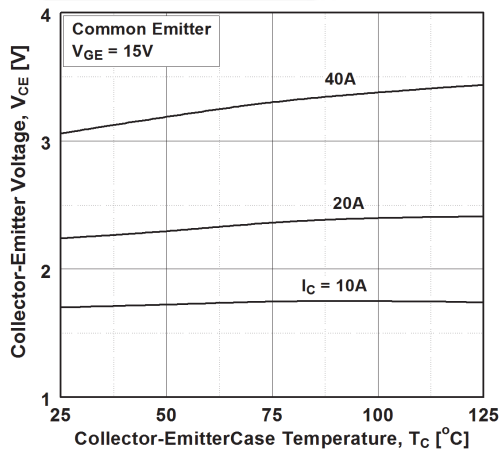
**Figure 3. Typical Saturation Voltage Characteristics**



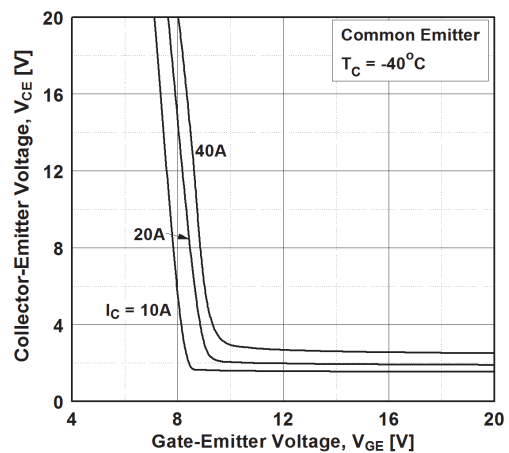
**Figure 4. Transfer Characteristics**



**Figure 5. Saturation Voltage vs. Case Temperature at Variant Current Level**



**Figure 6. Saturation Voltage vs. Vge**



## Typical Performance Characteristics

Figure 7. Saturation Voltage vs.  $V_{GE}$

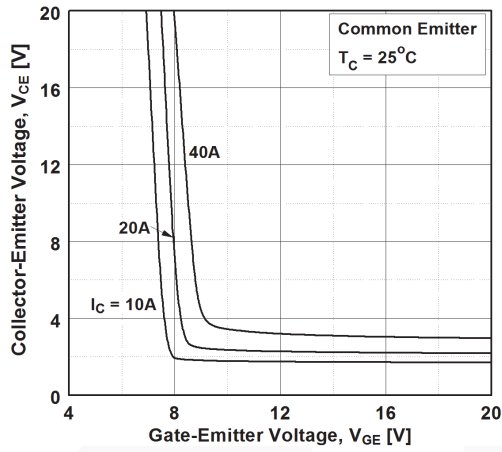


Figure 8. Saturation Voltage vs.  $V_{GE}$

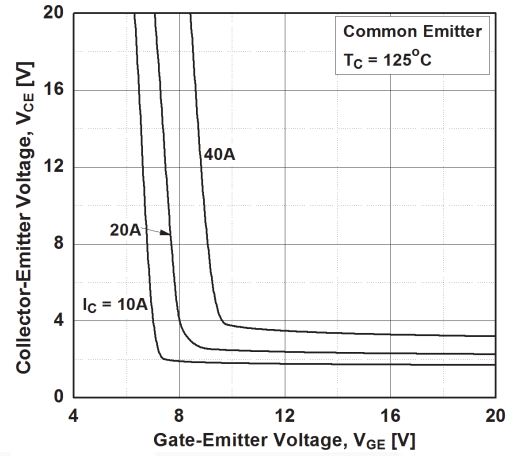


Figure 9. Capacitance Characteristics

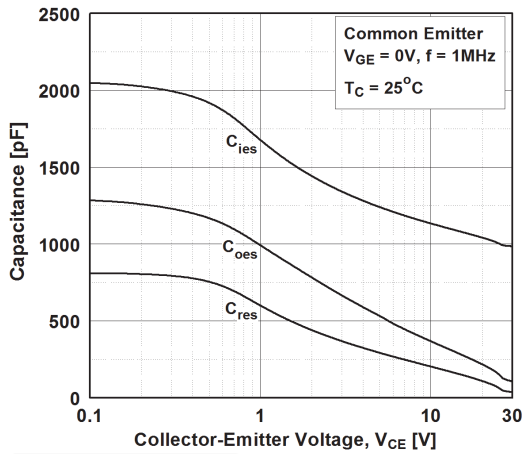


Figure 10. Gate charge Characteristics

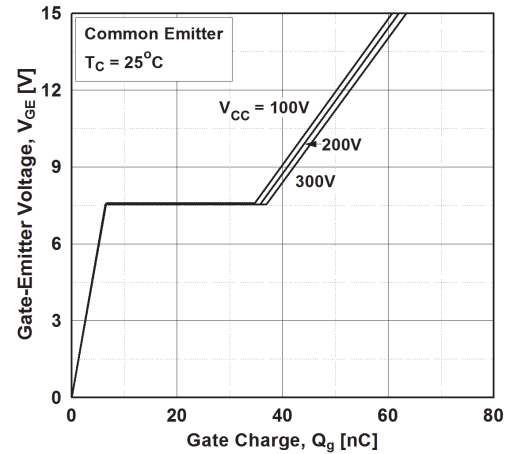


Figure 11. SOA Characteristics

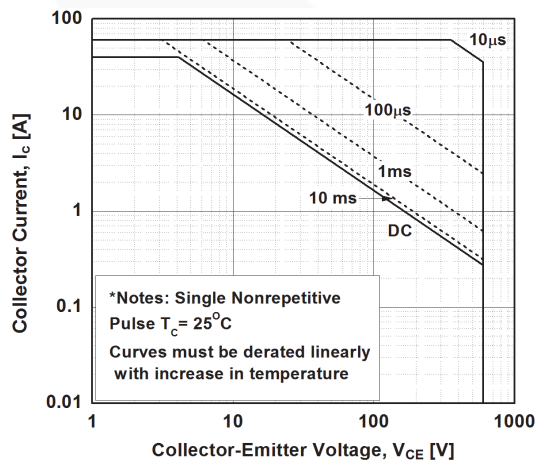
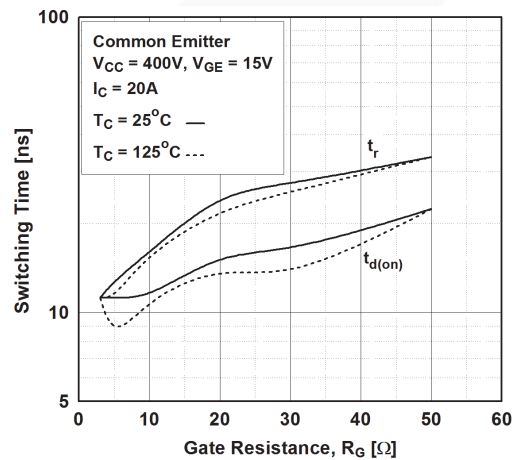
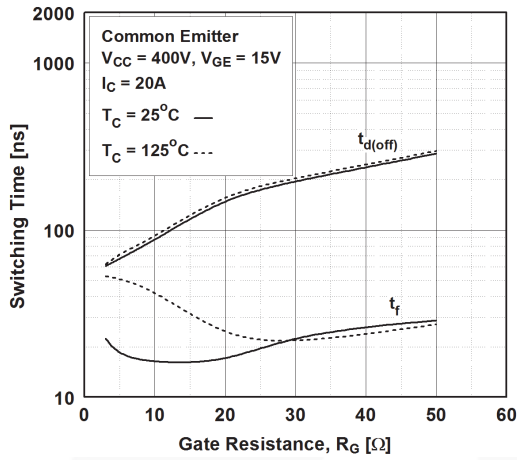


Figure 12. Turn-on Characteristics vs. Gate Resistance

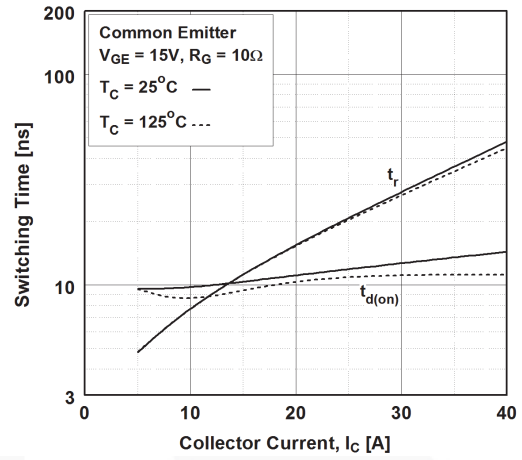


## Typical Performance Characteristics

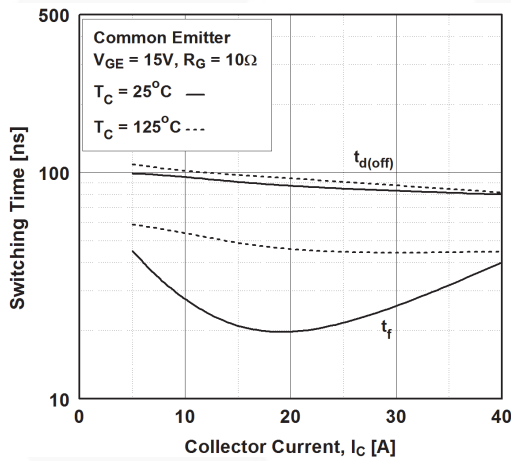
**Figure 13. Turn-off Characteristics vs. Gate Resistance**



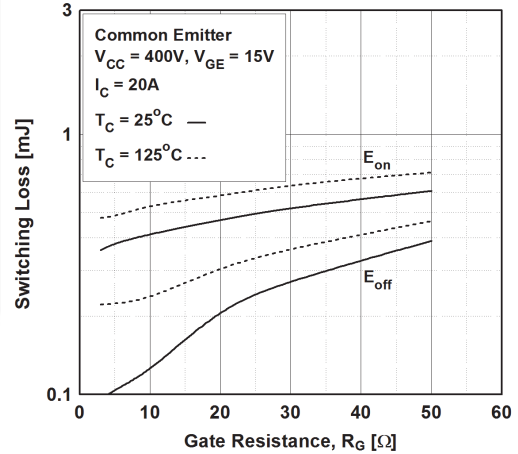
**Figure 14. Turn-on Characteristics vs. Collector Current**



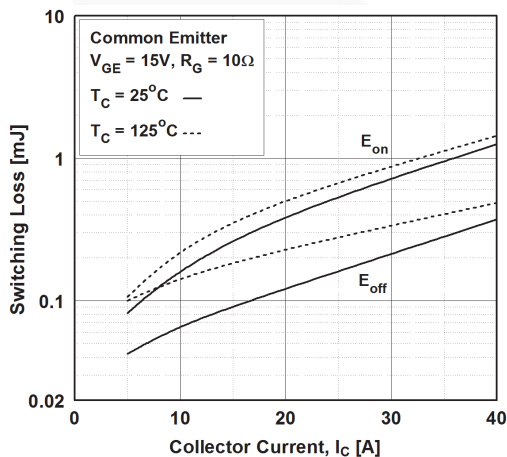
**Figure 15. Turn-off Characteristics vs. Collector Current**



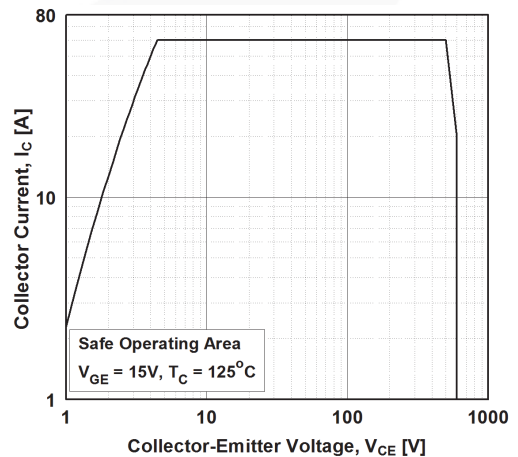
**Figure 16. Switching Loss vs. Gate Resistance**



**Figure 17. Switching Loss vs. Collector Current**



**Figure 18. Turn off Switching SOA Characteristics**



### Typical Performance Characteristics

Figure 19. Forward Characteristics

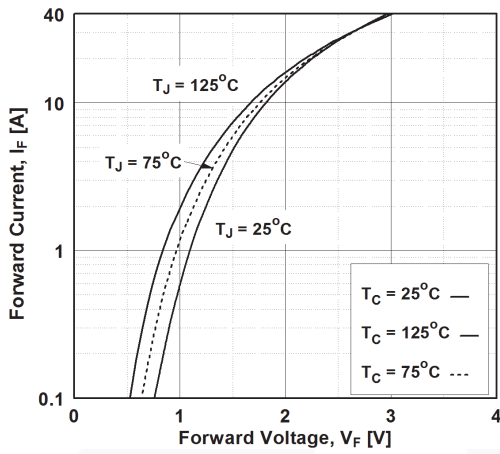


Figure 20. Reverse Current

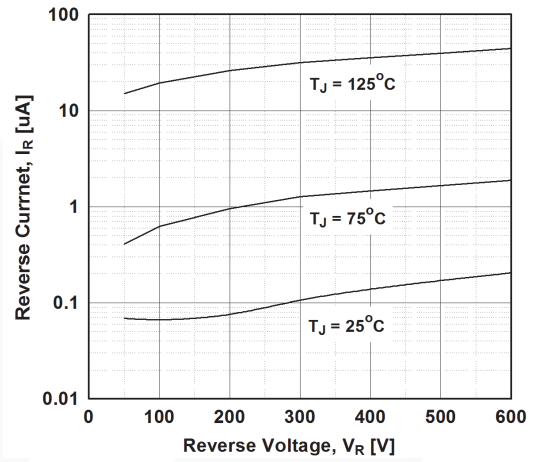


Figure 21. Stored Charge

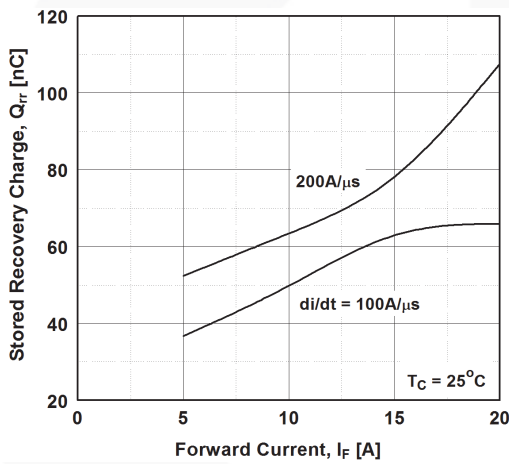


Figure 22. Reverse Recovery Time

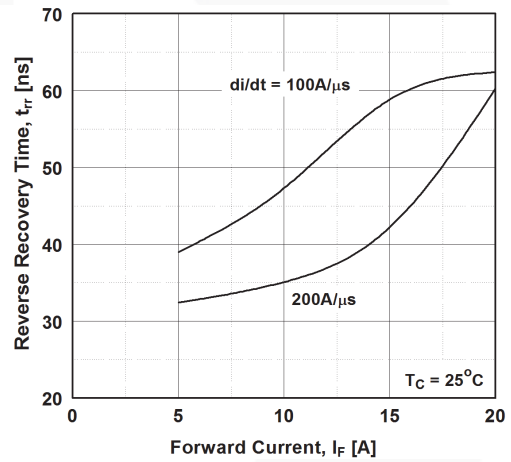
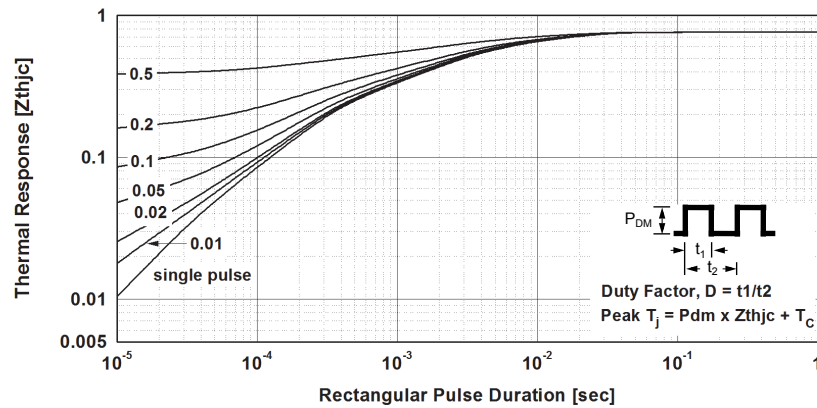
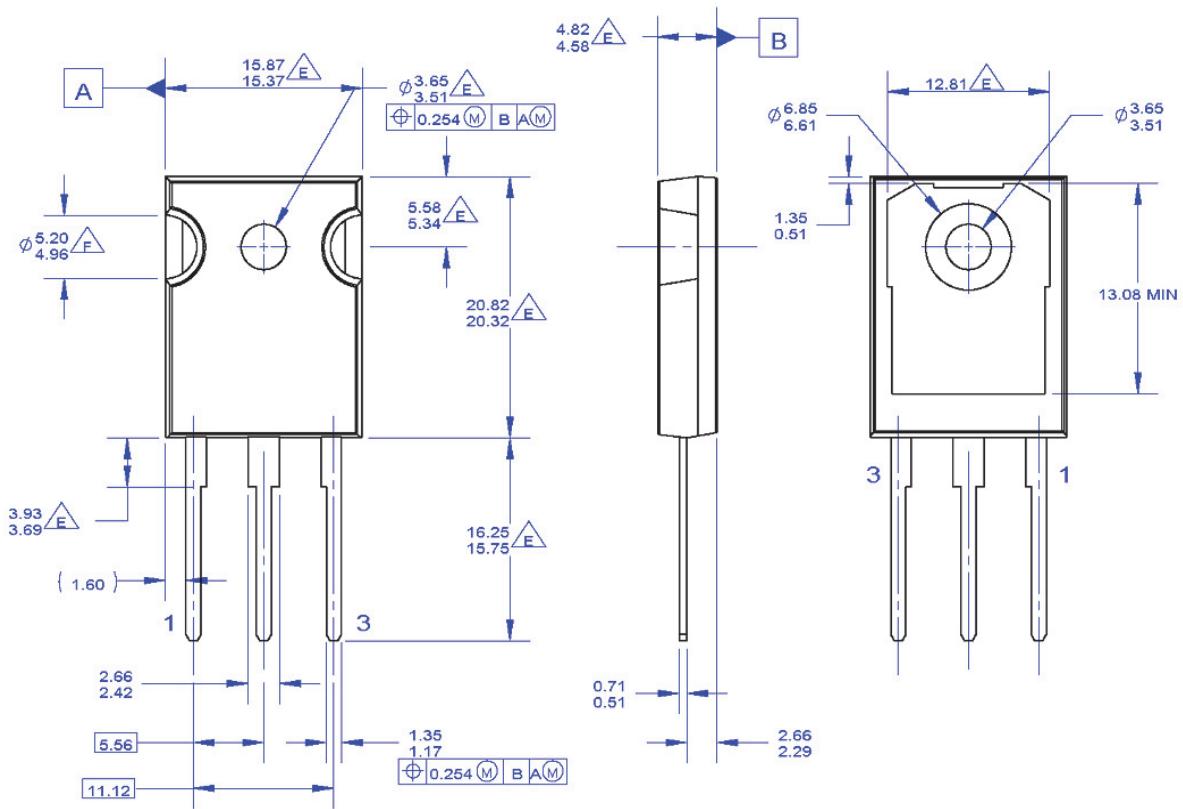


Figure 23. Transient Thermal Impedance of IGBT



**Mechanical Dimensions**



NOTES: UNLESS OTHERWISE SPECIFIED.

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- B. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
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**Figure 24. TO-247 3L - TO-247,MOLDED,3 LEAD,JEDEC VARIATION AB**

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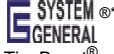



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| ESBC™   | MicroPak2™                                      | SMART START™  |  |
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| Fairchild®  | MotionMax™                                      | SPM®  | Ultra FRFET™  |
| Fairchild Semiconductor®  | MotionGrid®                                     | STEALTH™  | UniFET™   |
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| FACT®   | MTx®  | SuperSOT™-3   | VisualMax™  |
| FAST®   | MVN®  | SuperSOT™-6   | VoltagePlus™  |
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| FETBench™   | OptoHiT™  | SupreMOS®   | Xsens™  |
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No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
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